

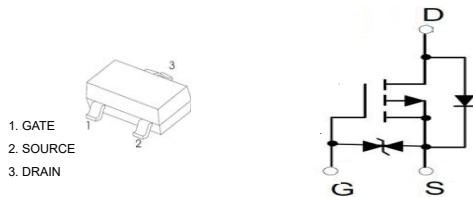
Feature

Surface Mount Package
P-Channel Switch with Low $R_{DS(on)}$
Operated at Low Logic Level Gate Drive

Application

Load/Power Switching
Interfacing, Logic Switching
Battery Management for Ultra Small Portable Electronics

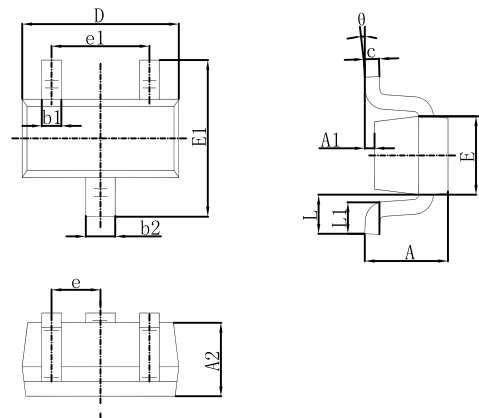
MARKING: 39K



Product Summary

$V_{(BR)DSS}$	$R_{DS(on)MAX}$	I_D
-20V	510mΩ@-4.5V	-0.75A
	750mΩ@-2.5V	
	960mΩ(TYP)@-1.8V	

SOT-523



Symbol	Dimensions in Millimeters		Dimensions in Inches	
	Min.	Max.	Min.	Max.
A	0.700	0.900	0.028	0.035
A1	0.000	0.100	0.000	0.004
A2	0.700	0.800	0.028	0.031
b1	0.150	0.250	0.006	0.010
b2	0.250	0.350	0.010	0.014
c	0.100	0.200	0.004	0.008
D	1.500	1.700	0.059	0.067
E	0.700	0.900	0.028	0.035
E1	1.450	1.750	0.057	0.069
e	0.500 TYP.		0.020 TYP.	
e1	0.900	1.100	0.035	0.043
L	0.400 REF.		0.016 REF.	
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°

Dimensions in inches and (millimeters)

ABSOLUTE MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	-20	V
Gate-Source Voltage	V_{GS}	±8	V
Continuous Drain Current	I_D	-0.75	A
Pulsed Drain Current ⁽¹⁾	I_{DM}	-1.2	A
Power Dissipation ⁽²⁾	P_D	150	mW
Thermal Resistance from Junction to Ambient ⁽¹⁾	$R_{\theta JA}$	833	°C/W
Junction Temperature	T_J	150	°C
Storage Temperature	T_{STG}	-55~ +150	°C

3139K

MOSFET ELECTRICAL CHARACTERISTICS($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Static Characteristics						
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = -250\mu A$	-20			V
Zero gate voltage drain current	I_{DSS}	$V_{DS} = -20V, V_{GS} = 0V$			-1	μA
Gate-body leakage current	I_{GSS}	$V_{GS} = \pm 10V, V_{DS} = 0V$			± 20	μA
Gate threshold voltage ⁽³⁾	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\mu A$	-0.35	-0.61	-1.1	V
Drain-source on-resistance ⁽³⁾	$R_{DS(on)}$	$V_{GS} = -4.5V, I_D = -1A$		420	510	m Ω
		$V_{GS} = -2.5V, I_D = -0.8A$		630	750	
		$V_{GS} = -1.8V, I_D = -0.5A$		960		
Forward tranconductance	g_{FS}	$V_{DS} = -10V, I_D = -0.54A$	0.8			S
Dynamic characteristics ⁽⁴⁾						
Input Capacitance	C_{iss}	$V_{DS} = -16V, V_{GS} = 0V, f = 1MHz$		113		pF
Output Capacitance	C_{oss}			15		
Reverse Transfer Capacitance	C_{rss}			9		
Switching Characteristics ⁽⁴⁾						
Turn-on delay time	$t_{d(on)}$	$V_{DS} = -10V, I_D = -200mA,$ $V_{GS} = -4.5V, R_G = 10\Omega$		9		ns
Turn-on rise time	t_r			5.7		
Turn-off delay time	$t_{d(off)}$			32.6		
Turn-off fall time	t_f			20.3		
Source-Drain Diode characteristics						
Diode forward voltage ⁽³⁾	V_{DS}	$I_S = -0.5A, V_{GS} = 0V$			-1.2	V

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. This test is performed with no heat sink at $T_a=25^{\circ}\text{C}$.
3. Pulse Test : Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 0.5\%$.
4. These parameters have no way to verify.

RATING AND CHARACTERISTIC CURVES (3139K)

